

AP03N40AP-HF

Halogen-Free Product

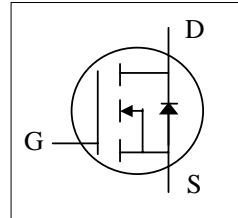


**Advanced Power
Electronics Corp.**

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

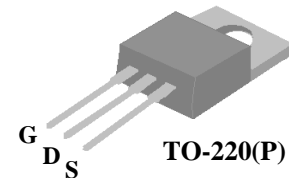
- ▼ 100% Avalanche Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	400V
$R_{DS(ON)}$	2.6 Ω
I_D	2.7A

Description

The AP03N40A provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.



The TO-220 package is widely preferred for commercial-industrial applications. The good thermal performance and low package cost, Contribute to its wide industry application.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	400	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.7	A
I_{DM}	Pulsed Drain Current ¹	10	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	44.6	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	2.8	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ C/W$

Data & specifications subject to change without notice

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Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	400	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =1.3A	-	-	2.6	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =1.3A	-	2	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =320V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =1A	-	11	17.5	nC
Q _{gs}	Gate-Source Charge	V _{DS} =320V	-	2.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	5	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DD} =200V	-	8	-	ns
t _r	Rise Time	I _D =1A	-	4.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	17	-	ns
t _f	Fall Time	V _{GS} =10V	-	10	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	370	600	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	45	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	9	-	pF
R _g	Gate Resistance	f=1.0MHz	-	3.2	6.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1.3A, V _{GS} =0V	-	-	1.5	V
t _{rr}	Reverse Recovery Time ²	I _S =1A, V _{GS} =0V,	-	150	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	820	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.
 USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.
 APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED
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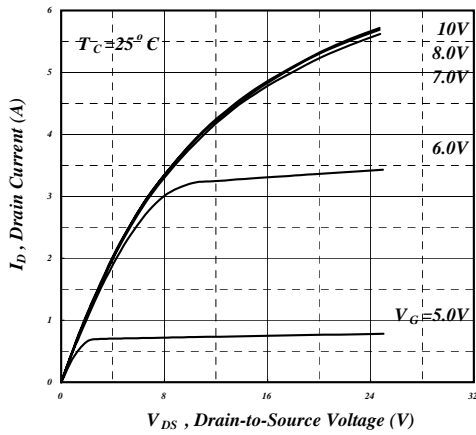


Fig 1. Typical Output Characteristics

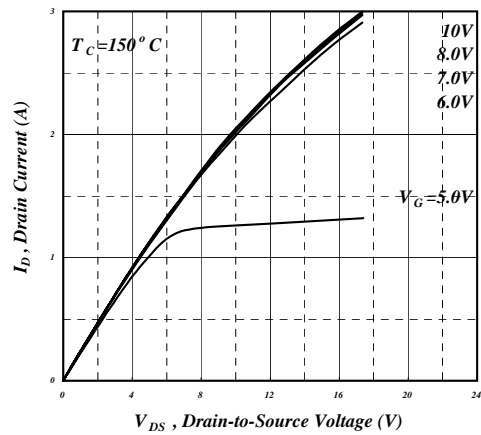


Fig 2. Typical Output Characteristics

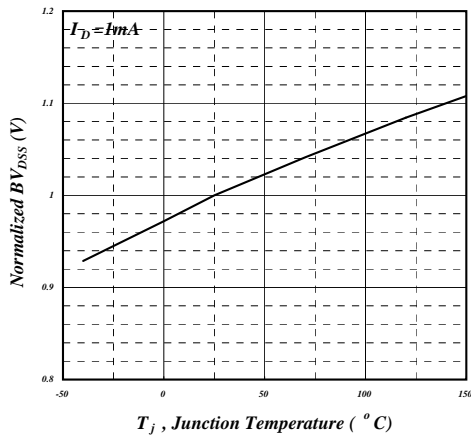


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

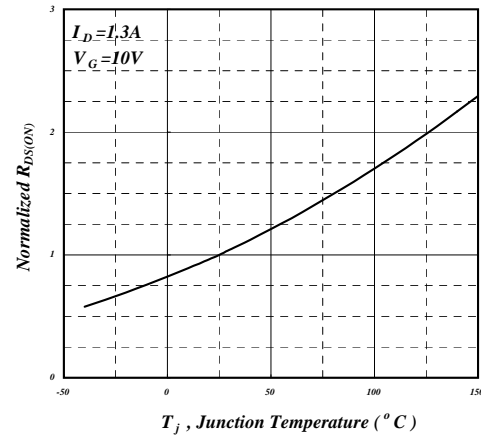


Fig 4. Normalized On-Resistance v.s. Junction Temperature

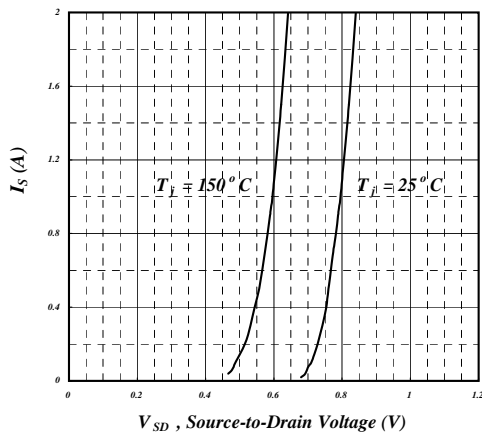


Fig 5. Forward Characteristic of Reverse Diode

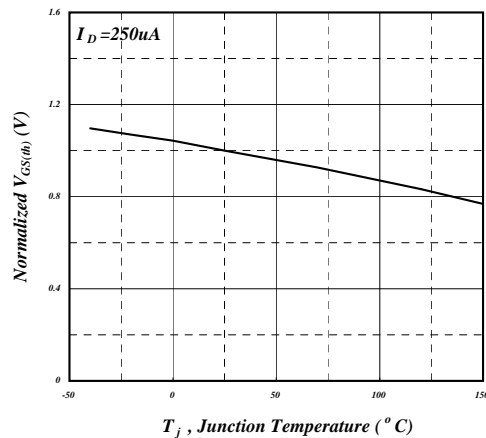


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



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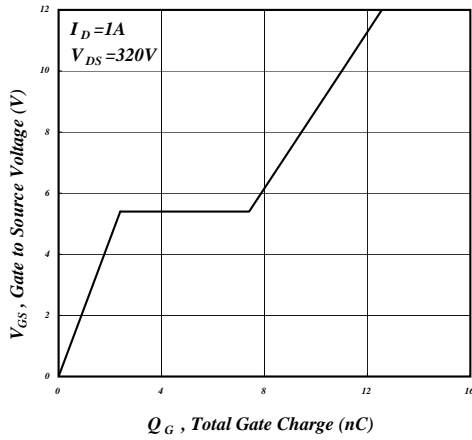


Fig 7. Gate Charge Characteristics

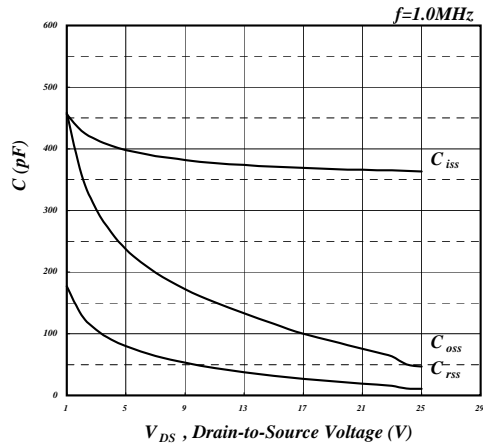


Fig 8. Typical Capacitance Characteristics

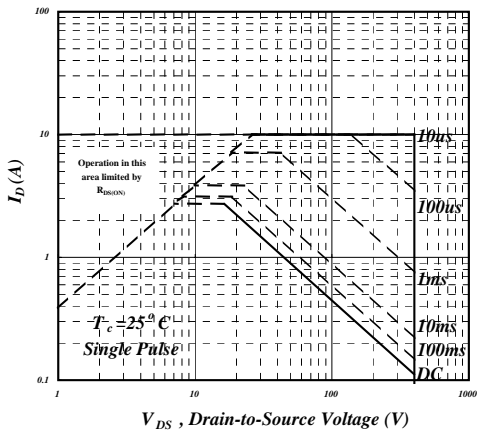


Fig 9. Maximum Safe Operating Area

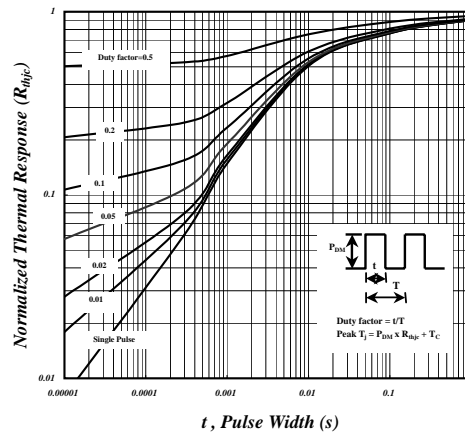


Fig 10. Effective Transient Thermal Impedance

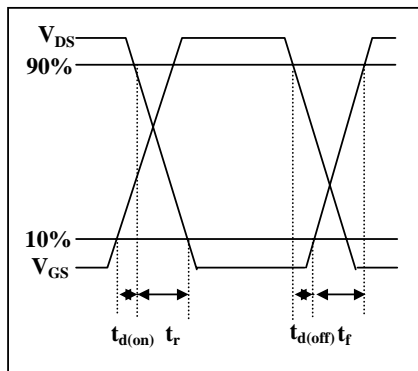


Fig 11. Switching Time Waveform

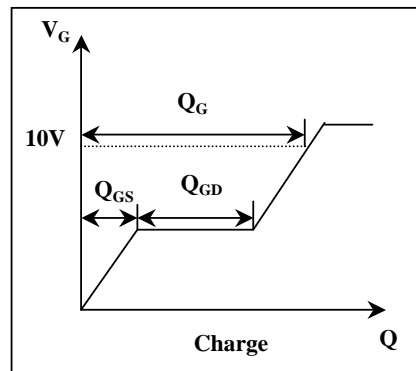


Fig 12. Gate Charge Waveform